







## **CMOS Monolithic Active Pixel Sensors**

A tool to measure open charm particles

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# Sherlock Holmes and Mystery of the Soup or How to build a webcam based carrot detector

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#### A Question to Sherlock Holmes



Prof. Dr. Johanna Wanka, Federal Minister of Research, Germany





The soup

The cook





#### How can one check that the soup has cooked?





Μ







**Dissolves** fast

Gets quickly soft if cooked

Gets slowly soft if cooked





Lets test ingredients, which keep information on the cooking process.





Dissolves also at room temperature

Keeps softening after cooking

Reacts slowly, might overlook cooking



#### The Quest of modern heavy ion experiments



We will have to test as many ingredients as possible to obtain a conclusive answer.



#### What means soup: Hadronic Matter



#### What means carrot: Observables



UrQMD transport calculation U+U 23 AGeV

## My topic today



#### How can

this technology help to...

#### find this...

#### in this!



## Why webcams?



## Why webcams



## Why webcams?



#### How does a webcam work?



#### The pre-amplifyer



#### Operation principle of the pre-amplifyer



Operation principle of the pre-amplifyer

#### Readout cycle in three steps:

First step: Readout-electronic-Man gives a Reset



When the basin is fully recharged, the water level is noted for reference.

Operation principle of the pre-amplifyer

Second step: Readout-elektronic-man has care for his other pixels now



Sometimes MIP-man passes by to take bucket of positiv charge (electrons are collected by the diode after a hit).

#### The operation principle of the pre-amplifyer

Third step: Readout-elektronik-man returns to check the water-level in the basin.



The level has dropped => MIP-man must have passed by.

MAPS pixels may measure even if they are disconnected from readout electronics and power supply.

#### Some sources of uncertainty



#### Relation between model and schematics



#### Readout system of early MAPS



## Comparing pixel sizes



#### MAPS: The operation principle



## The meaning of thin...



- 50 µm thickness
- Bended due to inner tensions
- Flexible silicon!

#### **Open charm reconstruction: Concept**



## Established pixel detector technologies (2003)



|                                    | Required<br>(CBM)  | CCD                 |
|------------------------------------|--------------------|---------------------|
| Single point res. [µm]             | ~ 5                | ~ 5                 |
| Material budget [X <sub>0</sub> ]  | ~ 0.3%             | ~0.1%               |
| Time resolution [µs]               | few 10             | ~100                |
| Rad. hardness [n/cm <sup>2</sup> ] | > 10 <sup>13</sup> | << 10 <sup>10</sup> |

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#### Requirements vs. detector performances (2003)



|                                    | Required           | Hybrid<br>pixels    | CCD                 |
|------------------------------------|--------------------|---------------------|---------------------|
| Single point res. [µm]             | ~ 5                | ~ 30                | ~ 5                 |
| Material budget [X <sub>0</sub> ]  | ~ 0.3%             | ~ 1%                | ~ 0.1%              |
| Time resolution [µs]               | few 10             | 0.025               | ~100                |
| Rad. hardness [n/cm <sup>2</sup> ] | > 10 <sup>13</sup> | >> 10 <sup>14</sup> | << 10 <sup>10</sup> |

#### Performances of MAPS (2003)

# MAPS provide an unique compromise between:

- sensitivity
- high rate capability



|                                    | Required           | Hybrid<br>pixels    | CCD                 | MAPS**<br>(2011)   |
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\*Sensor only \*\*Best of all prototypes



## X<sub>0</sub> and multiple scattering

#### **D**efinition of the radiation length (X<sub>0</sub>):

- Distance in a material, which decelerates charged particles with  $\gamma \gg 2000$  to 1/e of its energy.
- Material constant, tables available at <u>http://pdg.lbl.gov</u>

#### **R**elevance of the radiation length (X<sub>0</sub>):



1) The thinner, the better. 2)  $1\% X_0 = 1$ mm silicon

#### What means n<sub>ea</sub>/cm<sup>2</sup>?



#### **Radiation tolerance**



#### What about radiation hardness?

#### *lonising radiation:*

- Energy deposited into the electron cloud
- May ionise atoms and destroy molecules
- Caused by charged particles and photons





Non-ionising radiation:

- Energy deposited into the crystal lattice
- Atoms get displaced
- Caused by heavy (fast leptons, hadrons) charged and neutral particles

Farnan I, HM Cho, WJ Weber, 2007. "Quantification of Actinide  $\alpha$ -Radiation Damage in Minerals and Ceramics." *Nature* 445(7124):190-193.

#### Sensor R&D: Tolerance to non-ionising radiation



#### Sensor R&D: Tolerance to non-ionising radiation



Key observation: Signal amplitude is reduced by bulk damage

#### Sensor R&D: Tolerance to non-ionising radiation



Electric field increases the radiation hardness of the sensor Draw back: Need CMOS-processes with low doping epitaxial layer

## S/N of MIMOSA-18 AHR (high resistivity epi-layer)





Plausible conclusion: Radiation tolerance ~10<sup>14</sup> n<sub>eq</sub>/cm<sup>2</sup> reached

Cooling required to operate heavily irradiated sensors

#### Noise and cooling



Cooling is needed to exploid the improved radiation tolerance Alternative solution: Fast integration times help

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#### **Applications of MAPS**



#### Need for Speed II: A new generation at the horizon



In standard CMOS sensors, no PMOS transistors are possible in pixel => No high level functions like discriminators ... => "slow"

#### Going beyond rolling shutter







Full CMOS is reached in modern 0.18µm processes with quad-well Exploited for IPHC – AROM sensors (discriminator on pixel)

- + Simple, cost efficient, widely available in industry
- + Industrial trend toward better epitaxial layers
- On pixel electronics limited by pixel surface

#### **SOI - Pixels**



Silicon-On-Insulator Pixel Detector (SOIPIX)

#### **SOI - Pixels**



- + Dedicated sensor silicon + dedicated electronics silicon
- + Conceptually more radiation tolerance possible
- Thick BOX Oxide may be vulnerable to radiation damage
- Still under early R&D, moderate industrial support

#### Latest news (Yasuo Arai, Vertex 2013)



Diffraction Enhanced (Low angle) Image



## 3D VLSI integration, the best of all worlds



- Individual chips form always a compromise.
- 3D VLSI integration aims to pile chips and to connect them
- Potential: Get the best of all worlds

## How to put chips together (simplified)



- Drill holes (via) deep into the chips and fill with metal
- Thin silicon until vias are seen on back side
- Add "bond pads" on the back side
- Bond chips

## Status: (Ray Yarema, VERTEX2013)

- Prototypes submitted by large community, coordinated by Fermilab
- Industry failed with bonding => Years of delays and desasters
- Finally, few months ago:





- First individual working devices delivered and tested
- Problems are understood:
  - a) Don't take industry by the letter
  - b) Use bigger "through vias" to ease alignment while bonding
- Future submissions should be much easier

Ray Yarema: In hindsight, ..., we might have saved ~ 2 years and avoided a lot of grief. That's why it is called research.

## The final question: How to do system integration

Again, this structure will be fixed with

the novel Anti Gravitation Glue™.





#### Outlook: The story has just started





## Outlook: The story has just started

Idea from R. De Oliveira, W.Dulinski





#### SERNWIETE (mechanical demonstrator) A bended MIMOSA-26 in a foil

#### My collaborators:



**IPHC** PICSEL group, IPHC Strasbourg

AG Prof. Stroth, Goethe University Frankfurt

What else should have been mentioned:

I. Peric, ZITI, Heidelberg – Partially depleted 2.5D MAPS

V. Re et al, INFN, Pavia, Bergamo – MAPS with discriminator/shaper ... ând many others...